

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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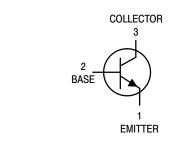
MPS2222A is a Preferred Device

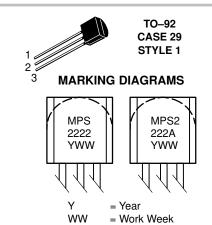
General Purpose Transistors

NPN Silicon



http://onsemi.com





MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MPS2222 MPS2222A	VCEO	30 40	Vdc
Collector–Base Voltage MPS2222 MPS2222A	V _{CBO}	60 75	Vdc
Emitter-Base Voltage MPS2222 MPS2222A	V _{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	IC	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta J A}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W

ORDERING INFORMATION

Device	Package	Shipping
MPS2222	TO-92	5000 Units/Box
MPS2222A	TO-92	5000 Units/Box
MPS2222ARLRA	TO-92	2000/Tape & Reel
MPS2222ARLRM	TO-92	2000/Ammo Pack
MPS2222ARLRP	TO-92	2000/Ammo Pack
MPS2222RLRA	TO-92	2000/Tape & Reel
MPS2222RLRM	TO-92	2000/Ammo Pack
MPS2222RLRP	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		-		•	
Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	MPS2222 MPS2222A	V _(BR) CEO	30 40	_ _	Vdc
Collector–Base Breakdown Voltage (I _C = 10 μ Adc, I _E = 0)	MPS2222 MPS2222A	V _(BR) CBO	60 75	_ _	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 µAdc, I _C = 0)	MPS2222 MPS2222A	V _{(BR)EBO}	5.0 6.0	_ _	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MPS2222A	ICEX	_	10	nAdd
Collector Cutoff Current (VCB = 50 Vdc, IE = 0) (VCB = 60 Vdc, IE = 0) (VCB = 50 Vdc, IE = 0, TA = 125°C) (VCB = 50 Vdc, IE = 0, TA = 125°C)	MPS2222 MPS2222A MPS2222 MPS2222A	ICBO	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (VEB = 3.0 Vdc, I _C = 0)	MPS2222A	IEBO	-	100	nAdc
Base Cutoff Current (VCE = 60 Vdc, VEB(off) = 3.0 Vdc)	MPS2222A	I _{BL}	_	20	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } T_{A}=-55^{\circ}\text{C}) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } T_{A}=-55^{\circ}\text{C}) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } T_{A}=-50^{\circ}\text{C}) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } T_{A}=-50^{\circ}\text{C}) \\ (I_C=150 \text{ mAdc, } T_{CE}=10 \text{ Vdc, } T_{CE}=10^{\circ}\text{C}) \\ (I_{C}=500 \text{ mAdc, } T_{CE}=10 \text{ Vdc, } T_{CE}=10^{\circ}\text{C}) \\ (I_{C}=500 \text{ mAdc, } T_{CE}=10 \text{ Vdc, } T_{CE}=10^{\circ}\text{C}) \\ \end{array} $	MPS2222A only MPS2222 MPS2222A	hFE	35 50 75 35 100 50 30 40	- - - 300 - - -	_
Collector–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	MPS2222 MPS2222A	V _{CE(sat)}	- -	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A		- -	1.6 1.0	
Base–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	MPS2222 MPS2222A	V _{BE(sat)}	_ 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A		<u>-</u>	2.6 2.0	

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit	
SMALL-SIGNAL CHARACTERISTICS	3					•
Current-Gain - Bandwidth Product (Note 2 (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 M	,	MPS2222 MPS2222A	fΤ	250 300	_ _	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, f = 1.0 MHz)		C _{obo}	_	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		MPS2222 MPS2222A	C _{ibo}	- -	30 25	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kH (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kH		MPS2222A MPS2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I _C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kH (I _C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kH		MPS2222A MPS2222A	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
Small–Signal Current Gain (I _C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kH (I _C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kH		MPS2222A MPS2222A	h _{fe}	50 75	300 375	_
Output Admittance (I _C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kH (I _C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kH		MPS2222A MPS2222A	h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (IE = 20 mAdc, V _{CB} = 20 Vdc, f = 31.8 M	IHz)	MPS2222A	rb′C _C	-	150	ps
Noise Figure (I _C = 100 μ Adc, V _{CE} = 10 Vdc, R _S = 1.0	kΩ, f = 1.0 kHz)	MPS2222A	NF	-	4.0	dB
SWITCHING CHARACTERISTICS N	IPS2222A only				•	
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$ $I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc}) \text{ (Figure 1)}$		t _d	_	10	ns
Rise Time			t _r	1	25	ns
	(V _{CC} = 30 Vdc, I _C = 150 mAdc, I _{B1} = I _{B2} = 15 mAdc) (Figure 2)		t _S	-	225	ns
Fall Time			t _f	_	60	ns

^{2.} f_T is defined as the frequency at which $|h_{\mbox{\scriptsize fe}}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

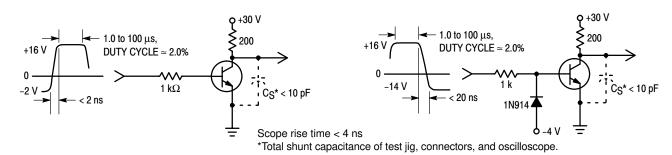


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

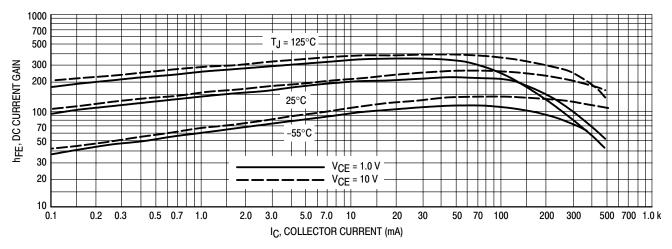


Figure 3. DC Current Gain

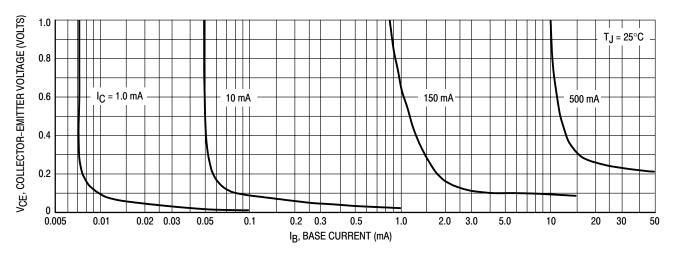


Figure 4. Collector Saturation Region

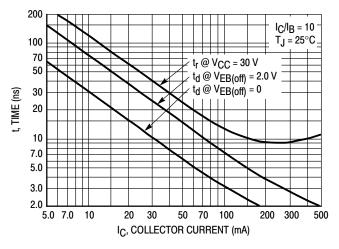


Figure 5. Turn-On Time

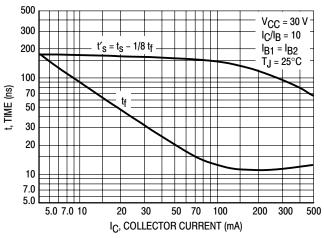


Figure 6. Turn-Off Time

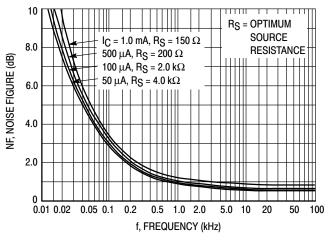


Figure 7. Frequency Effects

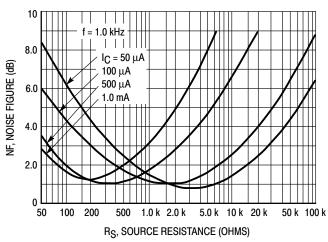


Figure 8. Source Resistance Effects

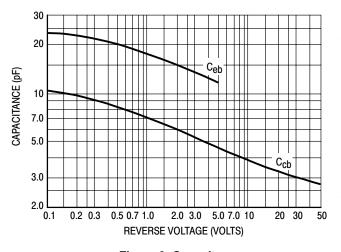


Figure 9. Capacitances

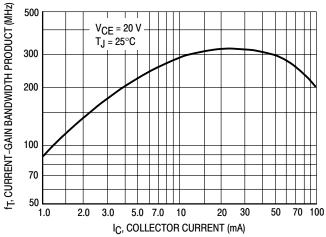
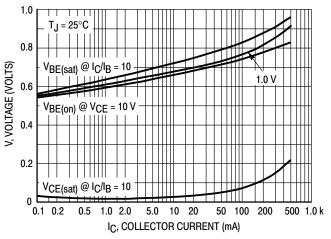


Figure 10. Current-Gain Bandwidth Product





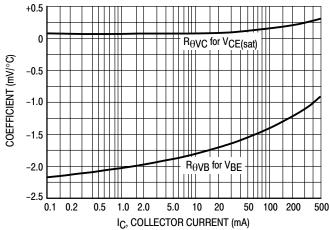
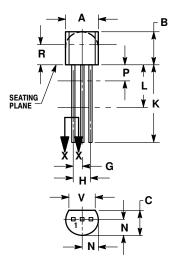


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 TO-226AA CASE 29-11

ISSUE AL





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

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